

## CR03AM-16

### Thyristor

Low Power Use

REJ03G0355-0100

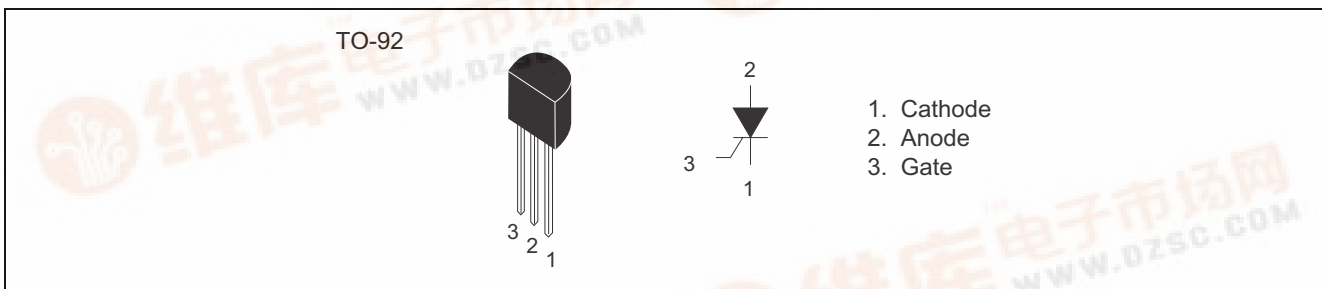
Rev.1.00

Aug.20.2004

### Features

- $I_{T(AV)}$  : 0.3 A
- $V_{DRM}$  : 800 V
- $I_{GT}$  : 100  $\mu$ A
- Non-Insulated Type
- Glass Passivation Type

### Outline



### Applications

Leakage protector, timer, and gas igniter

### Maximum Ratings

Parameter	Symbol	Voltage class	Unit
		16	
Repetitive peak reverse voltage	$V_{RRM}$	800	V
Non-repetitive peak reverse voltage	$V_{RSM}$	960	V
DC reverse voltage	$V_{R(DC)}$	640	V
Repetitive peak off-state voltage <sup>Note1</sup>	$V_{DRM}$	800	V
Non-repetitive peak off-state voltage <sup>Note1</sup>	$V_{DSM}$	960	V
DC off-state voltage <sup>Note1</sup>	$V_{D(DC)}$	640	V

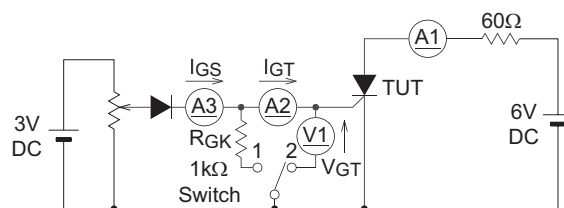
Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	$I_{T(RMS)}$	0.47	A	
Average on-state current	$I_{T(AV)}$	0.3	A	Commercial frequency, sine half wave 180° conduction, $T_a = 47^\circ\text{C}$
Surge on-state current	$I_{TSM}$	20	A	60Hz sine half wave 1 full cycle, peak value, non-repetitive
$I^2t$ for fusing	$I^2t$	1.6	$\text{A}^2\text{s}$	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	$P_{GM}$	0.5	W	
Average gate power dissipation	$P_{G(AV)}$	0.1	W	
Peak gate forward voltage	$V_{FGM}$	6	V	
Peak gate reverse voltage	$V_{RGM}$	6	V	
Peak gate forward current	$I_{FGM}$	0.3	A	
Junction temperature	$T_j$	-40 to +110	$^\circ\text{C}$	
Storage temperature	$T_{stg}$	-40 to +125	$^\circ\text{C}$	
Mass	—	0.23	g	Typical value

Notes: 1. With gate to cathode resistance  $R_{GK} = 1 \text{ k}\Omega$ .

## Electrical Characteristics

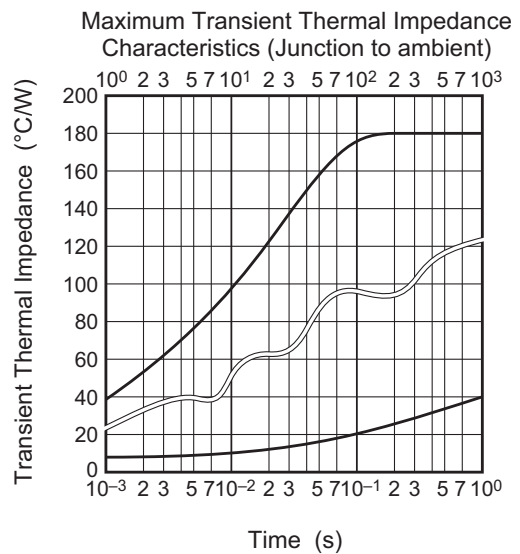
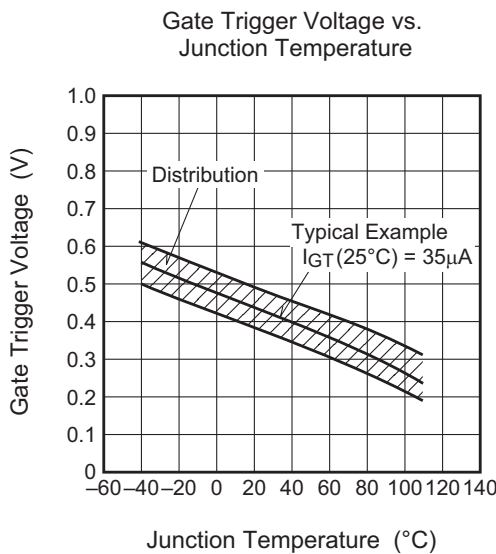
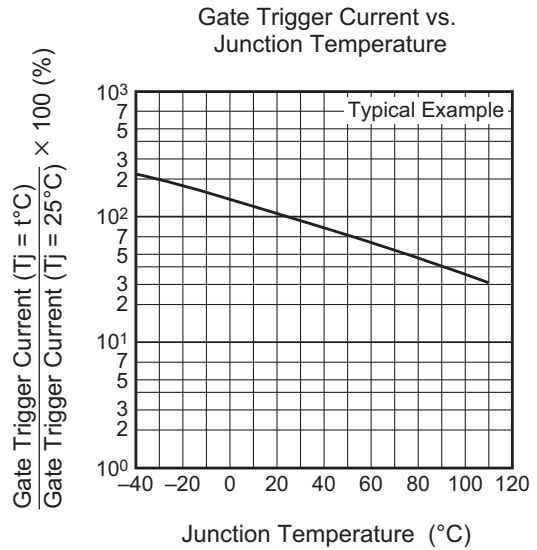
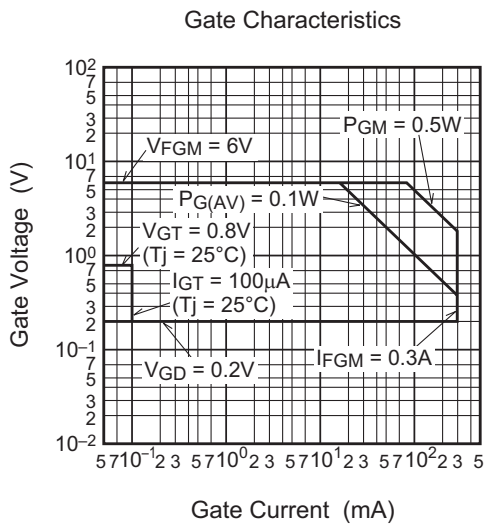
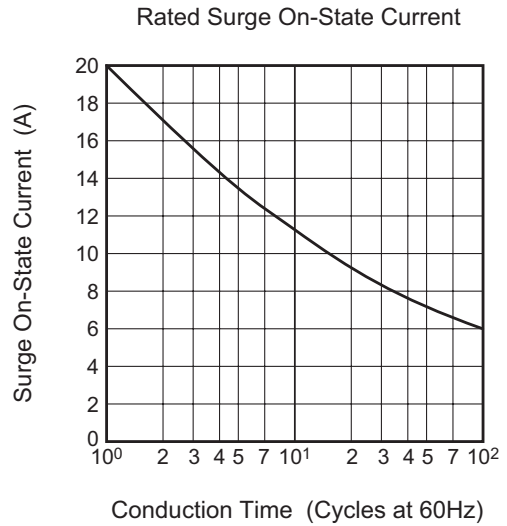
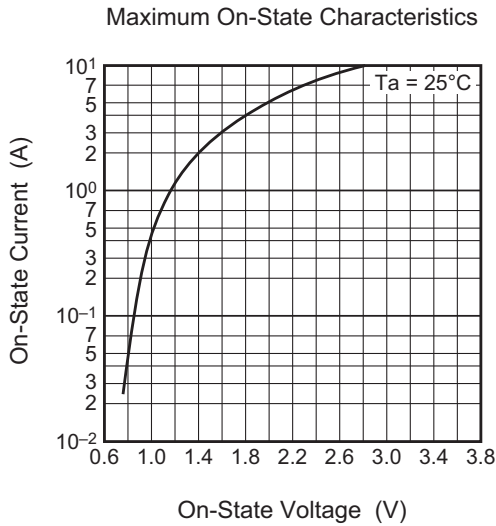
Parameter	Symbol	Rated value			Unit	Test conditions
		Min.	Typ.	Max.		
Repetitive peak reverse current	$I_{RRM}$	—	—	0.1	mA	$T_j = 110^\circ\text{C}$ , $V_{RRM}$ applied
Repetitive peak off-state current	$I_{DRM}$	—	—	0.1	mA	$T_j = 110^\circ\text{C}$ , $V_{DRM}$ applied, $R_{GK} = 1 \text{ k}\Omega$
On-state voltage	$V_{TM}$	—	—	1.8	V	$T_a = 25^\circ\text{C}$ , $I_{TM} = 4 \text{ A}$ , instantaneous value
Gate trigger voltage	$V_{GT}$	—	—	0.8	V	$T_j = 25^\circ\text{C}$ , $V_D = 6 \text{ V}$ , $I_T = 0.1 \text{ A}$ <sup>Note2</sup>
Gate non-trigger voltage	$V_{GD}$	0.2	—	—	V	$T_j = 110^\circ\text{C}$ , $V_D = 1/2 V_{DRM}$ , $R_{GK} = 1 \text{ k}\Omega$
Gate trigger current	$I_{GT}$	1	—	100	$\mu\text{A}$	$T_j = 25^\circ\text{C}$ , $V_D = 6 \text{ V}$ , $I_T = 0.1 \text{ A}$ <sup>Note2</sup>
Holding current	$I_H$	—	1.5	3	mA	$T_j = 25^\circ\text{C}$ , $V_D = 12 \text{ V}$ , $R_{GK} = 1 \text{ k}\Omega$
Thermal resistance	$R_{th(j-a)}$	—	—	180	$^\circ\text{C/W}$	Junction to ambient

Notes: 2.  $I_{GT}$ ,  $V_{GT}$  measurement circuit.



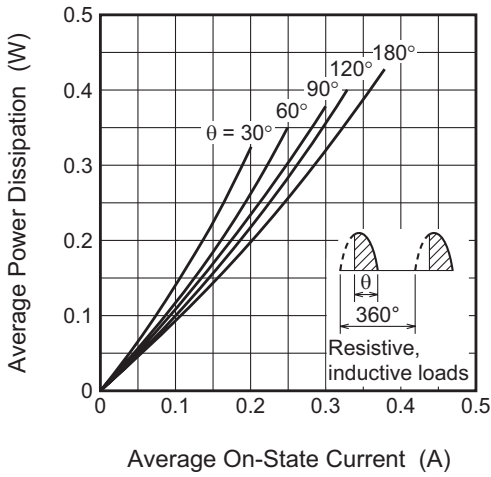
Switch 1 :  $I_{GT}$  measurement  
 Switch 2 :  $V_{GT}$  measurement  
 (Inner resistance of voltage meter is about  $1 \text{ k}\Omega$ )

Performance Curves  
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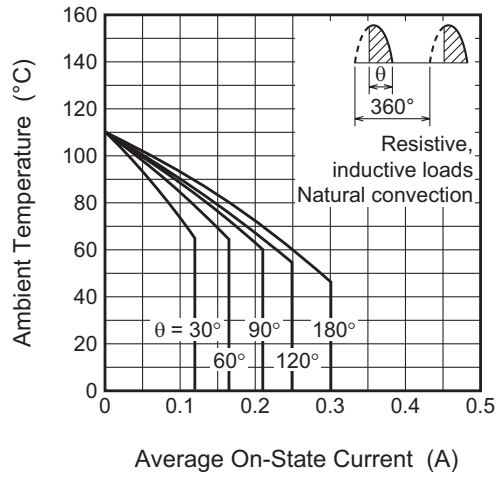


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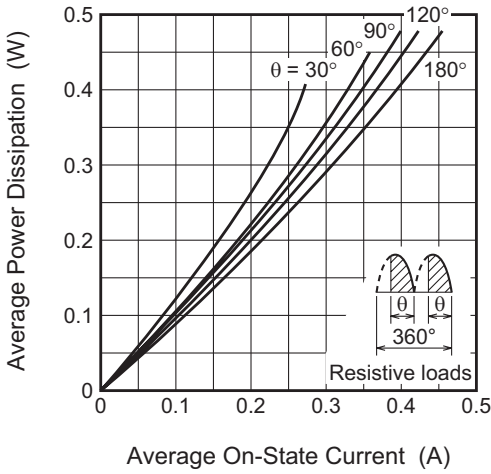
Maximum Average Power Dissipation  
(Single-Phase Half Wave)



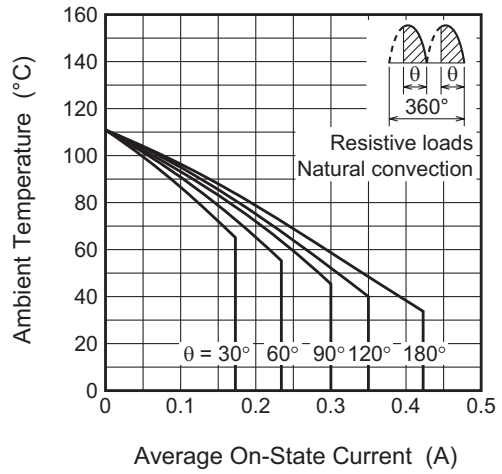
Allowable Ambient Temperature vs.  
Average On-State Current  
(Single-Phase Half Wave)



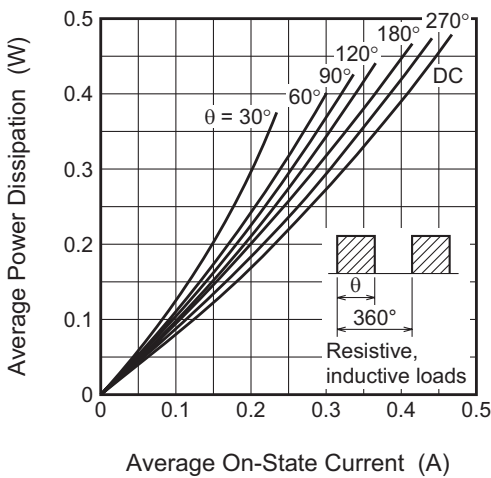
Maximum Average Power Dissipation  
(Single-Phase Full Wave)



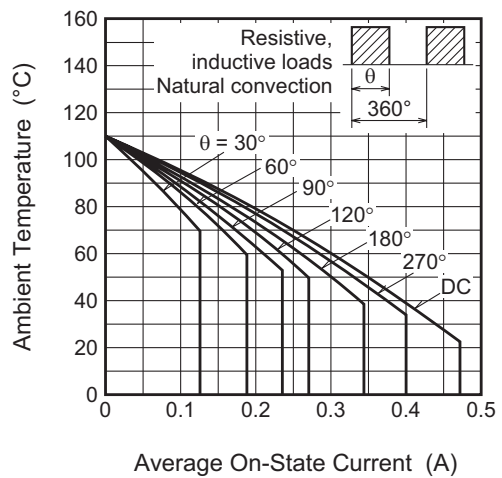
Allowable Ambient Temperature vs.  
Average On-State Current  
(Single-Phase Full Wave)



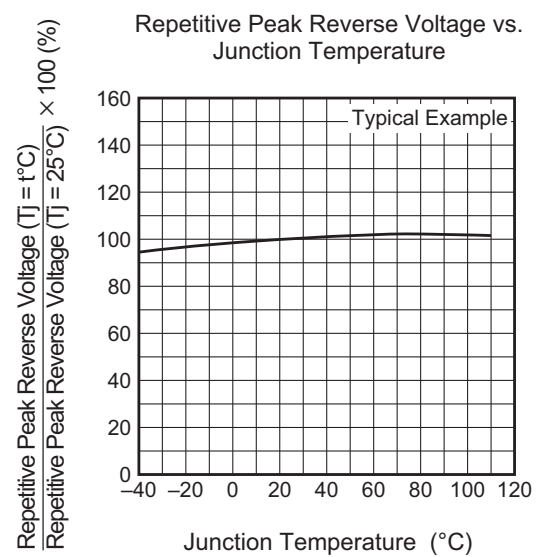
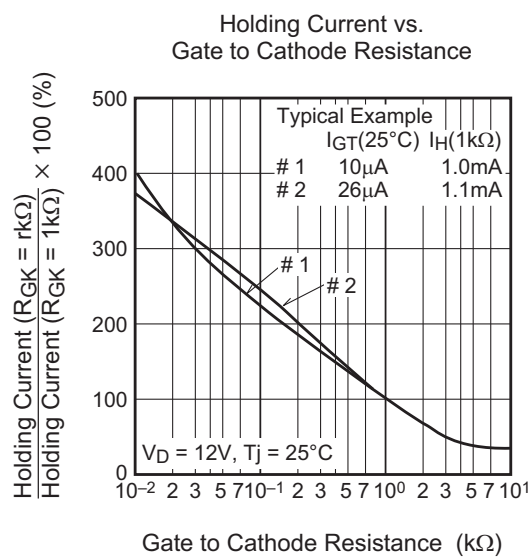
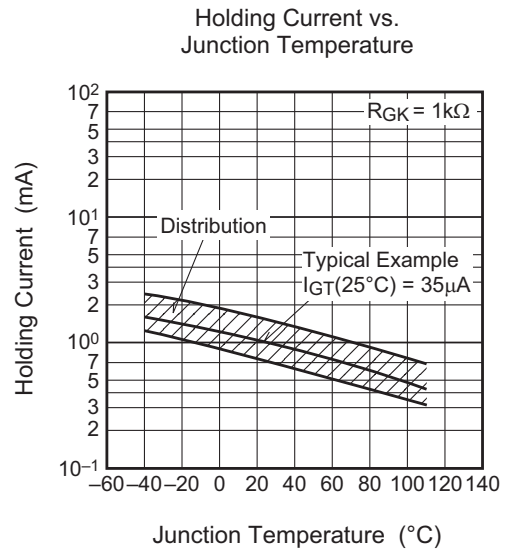
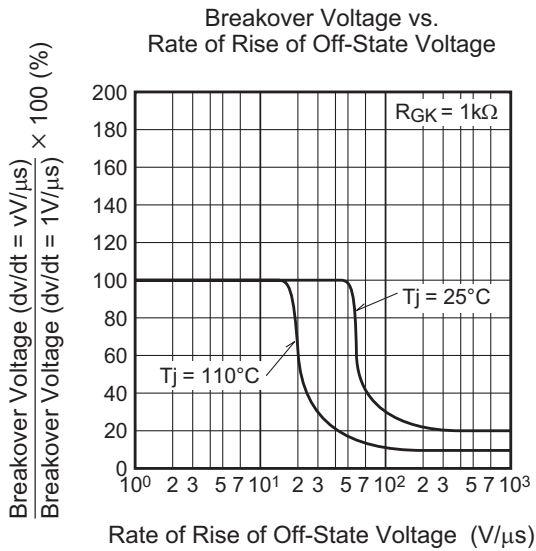
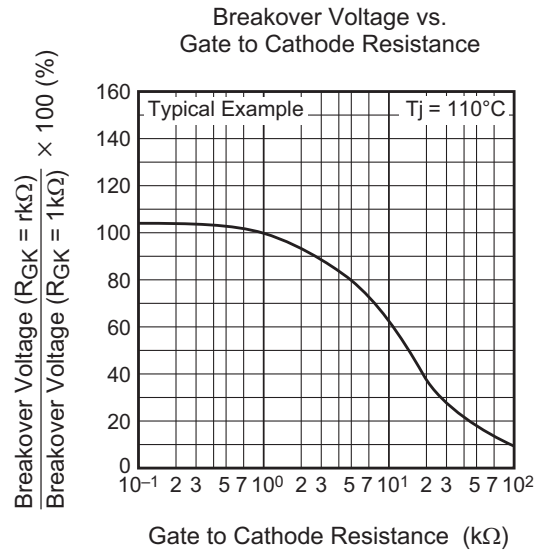
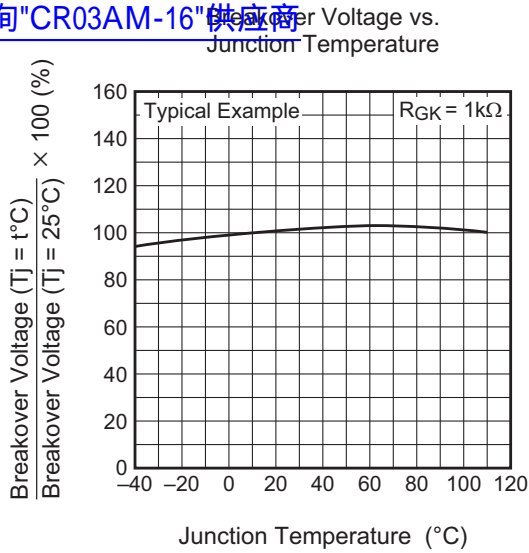
Maximum Average Power Dissipation  
(Rectangular Wave)



Allowable Ambient Temperature vs.  
Average On-State Current  
(Rectangular Wave)

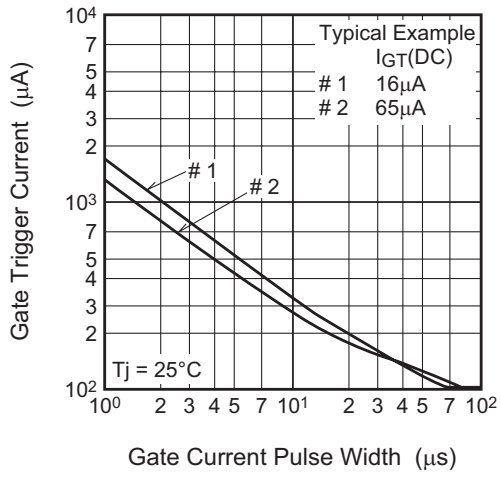


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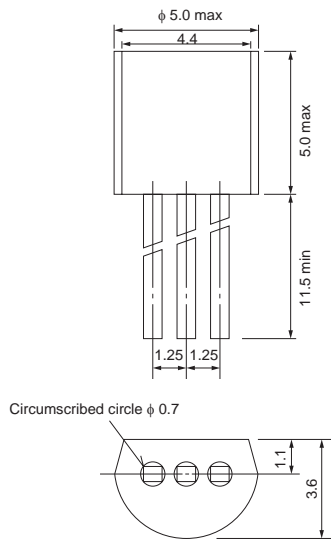
Gate Trigger Current vs. Gate Current Pulse Width



Package Dimensions 供应商

TO-92

EIAJ Package Code	JEDEC Code	Mass (g) (reference value)	Lead Material
Conforms	Conforms	0.23	Cu alloy



Symbol	Dimension in Millimeters		
	Min	Typ	Max
A	—	—	—
A <sub>1</sub>	—	—	—
A <sub>2</sub>	—	—	—
b	—	—	—
D	—	—	—
E	—	—	—
e	—	—	—
x	—	—	—
y	—	—	—
y <sub>1</sub>	—	—	—
ZD	—	—	—
ZE	—	—	—

Note 1) The dimensional figures indicate representative values unless otherwise the tolerance is specified.

Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	500	Type name	CR03AM-16
Lead form	Vinyl sack	500	Type name – Lead forming code	CR03AM-16-A6
Form A8	Taping	2000	Type name – TB	CR03AM-16-TB

Note : Please confirm the specification about the shipping in detail.

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